

## 1.Description

SS020N04NSL, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for motor drivers and high speed switching applications.

### KEY CHARACTERISTICS

Parameter	Value	Unit
V <sub>DSS</sub>	40	V
I <sub>D</sub>	130	A
R <sub>DS(on).typ</sub>	1.6	mΩ

### FEATURES:

- Fast Switching
- Low On-Resistance (  $R_{DS(on)} \leq 2.0m\Omega$  )
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

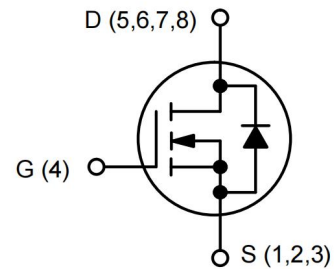
### APPLICATIONS:

- Switching applications
- Motor drivers
- BMS
- Synchronous rectification

### ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing	Quantity
SS020N04NSL	PDFN5x6	SS020N04NSL	Reel	5000

### Schematic Diagram



### PDFN5×6

